

1N5823 - 1N5825 SCHOTTKY BARRIER RECTIFIER DIODE

VOLTAGE RANGE: 20-40V

CURRENT: 5.0 A

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-201AD					
Dim	Min	Мах			
Α	25.40	_			
В	8.50	9.53			
С	0.96	1.06			
D	4.80	5.21			
All Dimensions in mm					

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

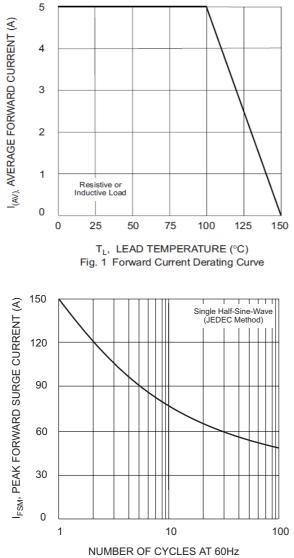
Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

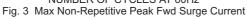
Characteristic	Symbol	1N5823	1N5824	1N5825	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	20	30	40	v
RMS Reverse Voltage	VR(RMS)	14	21	28	V
Average Rectified Output Current $@T_L = 100^{\circ}C$ (Note 1)	lo	5.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM		150		A
Forward Voltage $@I_F = 5.0A$	Vfm	0.55			V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Iгм	0.5 50			mA
Typical Junction Capacitance (Note 2)	Cj		500		pF
Typical Thermal Resistance (Note 1)	R∂JA		10		°C/W
Operating and Storage Temperature Range	Тј, Тѕтс		-65 to +150		°C

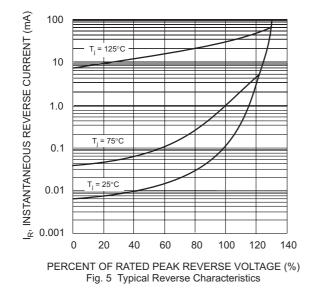
Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.









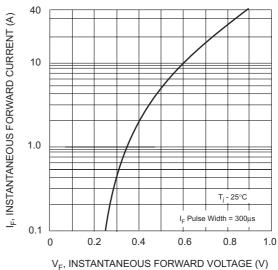


Fig. 2 Typical Forward Characteristics

